**Features:**

- n Isolated mounting base 3000V~
- n Pressure contact technology with Increased power cycling capability
- n Space and weight saving

Typical Applications

- n Inverter
- n Inductive heating
- n Chopper

V _{RRM}	Type & Outline
2000V	MZ250-20-417F2
2200V	MZ250-22-417F2
2500V	MZ250-25-417F2
2800V	MZ250-28-417F2
3000V	MZ250-30-417F2

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T _j (°C)	VALUE			UNIT
				Min	Type	Max	
I _{F(AV)}	Mean forward current	180° half sine wave 50Hz Single side cooled, T _C =85°C	140			250	A
I _{F(RMS)}	RMS forward current					392	A
I _{RRM}	Repetitive peak current	at V _{RRM}	140			50	mA
I _{FSM}	Surge forward current	10ms half sine wave V _R =0.6V _{RRM}	140			8	kA
I ² t	I ² t for fusing coordination					320	10 ³ A ² s
V _{FO}	Threshold voltage		140			1.85	V
r _F	Forward slope resistance					0.50	mW
V _{FM}	Peak forward voltage	I _{FM} =750A	25			2.67	V
t _{rr}	Reverse recovery time	I _{FM} =300A, t _p =4000μs, -di/dt=20A/μs, V _R =100V	140		4		μs
R _{th(j-c)}	Thermal resistance Junction to case	Single side cooled per chip				0.065	°C/W
R _{th(c-h)}	Thermal resistance case to heatsink	Single side cooled per chip				0.030	°C/W
V _{iso}	Isolation voltage	50Hz, R.M.S, t=1min, I _{iso} :1mA(MAX)		3000			V
F _m	Terminal connection torque(M10)			10		12	N·m
	Mounting torque(M6)			4.5		6.0	N·m
T _{vj}	Junction temperature			-40		140	°C
T _{stg}	Stored temperature			-40		125	°C
W _t	Weight				770		g
Outline	417F2						

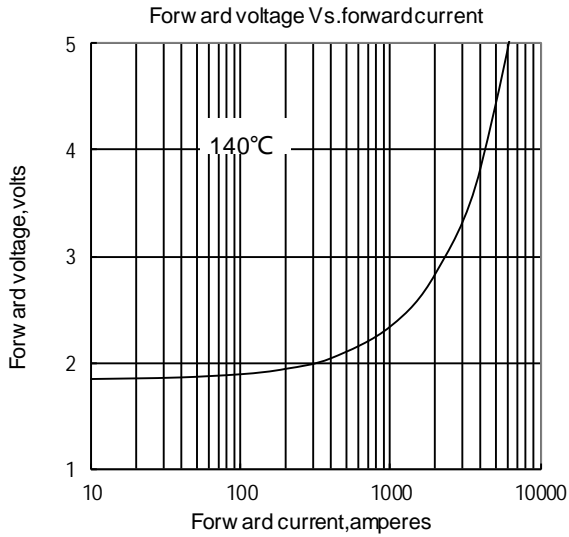


Fig.1

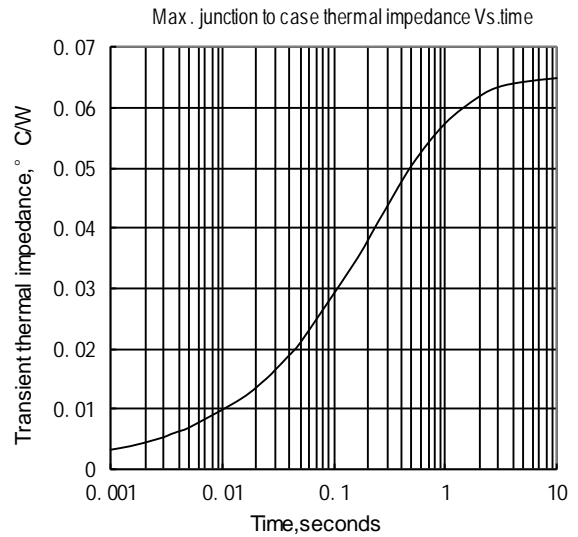


Fig.2

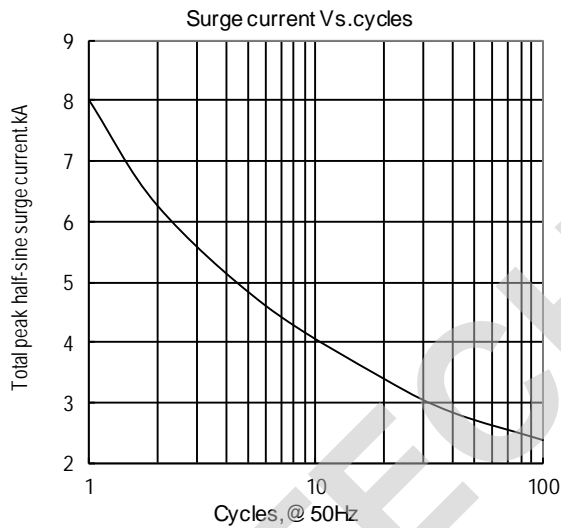


Fig.3

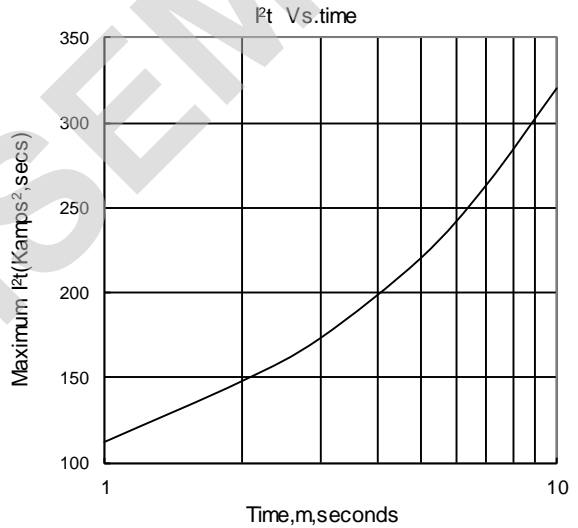
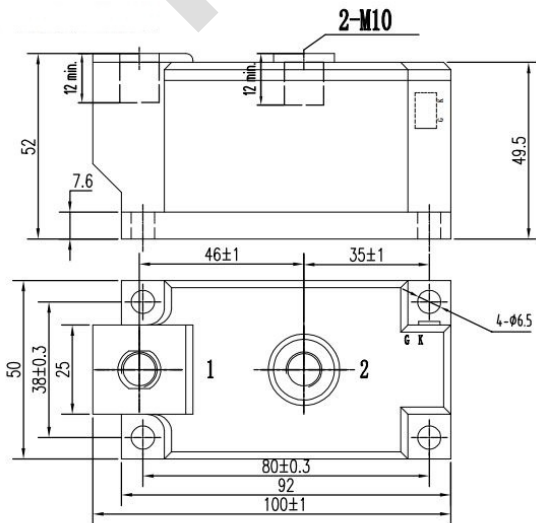


Fig.4

Outline:



Unmarked dimensional tolerance : ±0.5mm



TECHSEM reserves the right to change specifications without notice.